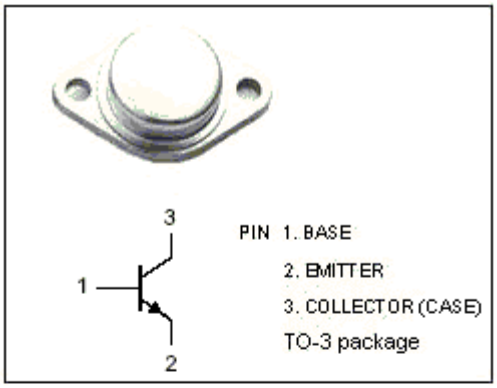
isc Silicon NPN Power Transistor 2SC2616

DESCRIPTION

- High Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$= 400V (Min)
- High Switching Speed

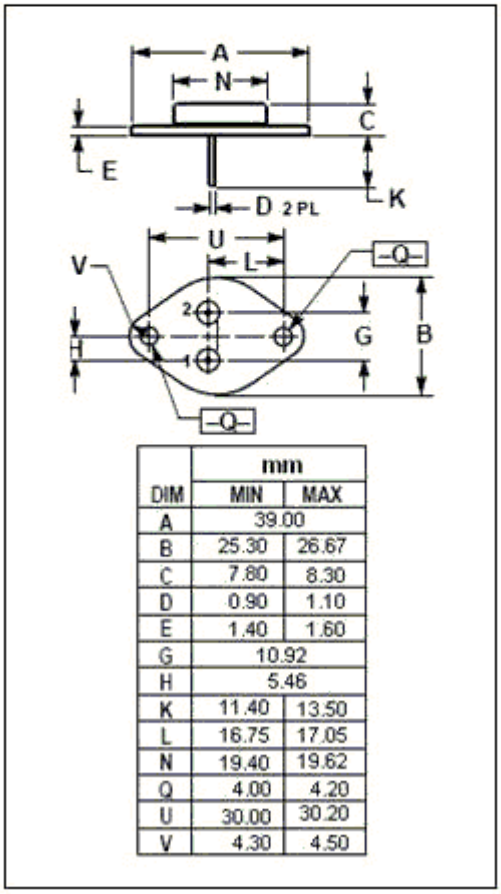


APPLICATIONS

- Designed for high voltage, high speed and high power switching applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	MAX	UNIT
V_{CBO}	Collector-Base Voltage	500	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	10	A
I_{CM}	Collector Current-Peak	20	A
I_B	Base Current-Continuous	5	A
P_C	Collector Power Dissipation @T_C=25℃	100	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.30
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.40	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustainig Voltage	I_C= 0.2A; R_{BE}= ∞; L= 100mH	400			V
$V_{CEX(SUS)}$	Collector-Emitter Sustainig Voltage	I_C= 5A; I_{B1}=-I_{B2}= 1A, V_{BE}= -5V; L=180μH,clamped	400			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 5A; I_B= 1A			1.2	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 5A; I_B= 1A			1.7	V
h_{FE-1}	DC Current Gain	I_C= 5A; V_{CE}= 5V	15			
h_{FE-2}	DC Current Gain	I_C= 10A; V_{CE}= 5V	7			
I_{CBO}	Collector Cutoff Current	V_{CB}= 400V; I_E= 0			0.1	mA
I_{CEO}	Collector Cutoff Current	V_{CE}= 350V; R_{BE}= ∞			0.1	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			0.1	mA

Switching Times

t_r	Rise Time	I_C= 10A; I_{B1}= -I_{B2}= 2A, V_{CC}≈ 150V			1.0	μs
t_{stg}	Storage Time				2.5	μs
t_f	Fall Time				1.0	μs